

KS54AHCT 390

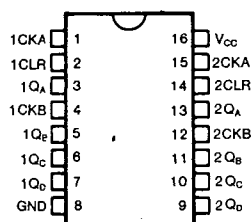
KS74AHCT

Dual 4-Bit Decade Counters

FEATURES

- Individual clock for A and B flip-flops provide dual +2 and +5 counters
- Direct clear for each 4-bit counter
- Significant improvement in system density through reduced counter package count.
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
($I_{OL} = 8 \text{ mA}$ @ $V_{OL} = 0.5\text{V}$)
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74HCTLS: -40°C to $+85^{\circ}\text{C}$
KS54HCTLS: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

PIN CONFIGURATION



FUNCTION TABLES

BCD COUNT SEQUENCE
(EACH COUNTER)
(See Note A)

COUNT	OUTPUT			
	Q _D	Q _C	Q _B	Q _A
0	L	L	L	L
1	L	L	L	H
2	L	L	H	L
3	L	L	H	H
4	L	H	L	L
5	L	H	L	H
6	L	H	H	L
7	L	H	H	H
8	H	L	L	L
9	H	L	L	H

BIQUINARY (5-2)
(EACH COUNTER)
(See Note B)

COUNT	OUTPUT			
	Q _D	Q _C	Q _B	Q _A
0	L	L	L	L
1	L	L	L	H
2	L	L	H	L
3	L	L	H	H
4	L	H	L	L
5	H	L	L	L
6	H	L	L	H
7	H	L	H	L
8	H	L	H	H
9	H	H	L	L

- NOTES A. Output Q_A is connected to input CKB for BCD count.
B. Output Q_D is connected to input CKA for biquinary count.



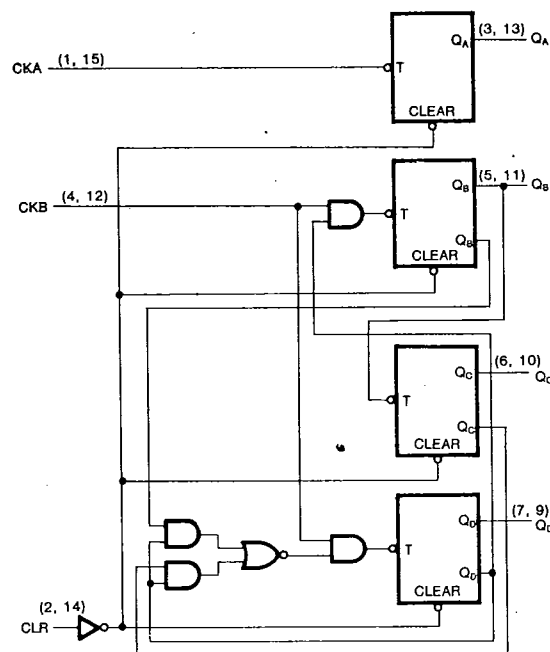
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KS54AHCT 390
KS74AHCT

Dual 4-Bit Decade Counters

T-45-23-13

LOGIC DIAGRAM

**Absolute Maximum Ratings***

Supply Voltage Range V_{CC} -0.5V to +7V
 DC Input Diode Current, I_{IK}
 $(V_I < -0.5V \text{ or } V_I > V_{CC} + 0.5V)$ ± 20 mA
 DC Output Diode Current, I_{OK}
 $(V_O < -0.5V \text{ or } V_O > V_{CC} + 0.5V)$ ± 20 mA
 Continuous Output Current Per Pin, I_O
 $(-0.5V < V_O < V_{CC} + 0.5V)$ ± 35 mA
 Continuous Current Through
 V_{CC} or GND pins ± 125 mA
 Storage Temperature Range, T_{stg} -65°C to +150°C
 Power Dissipation Per Package, P_d [†] 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

[†] Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V
 DC Input & Output Voltages*, V_{IN} , V_{OUT} ... 0V to V_{CC}
 Operating Temperature
 Range

KS74AHCT: -40°C to +85°C

KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t_r , t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)



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DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

DC ELECTRICAL CHARACTERISTICS (V _{CC} = 5V ± 10% unless otherwise specified)						
Characteristic	Symbol	Test Conditions	T _A = 25°C	KS74AHCT	KS54AHCT	Unit
			Typ	T _A = -40°C to +85°C	T _A = -55°C to +125°C	
Guaranteed Limits						
Minimum High-Level Input Voltage	V _{IH}		2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V _{IL}		0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL} I _O = -20μA I _O = -4mA	V _{CC} 4.2	V _{CC} - 0.1 3.98	V _{CC} - 0.1 3.7	V
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL} I _O = 20μA I _O = 4mA I _O = 8mA	0	0.1 0.26 0.39	0.1 0.33 0.5	V
Maximum Input Current	I _{IN}	V _{IN} = V _{CC} or GND	±0.1	±1.0	±1.0	μA
Maximum Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND I _{OUT} = 0μA	8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI _{CC}	per input pin V _I = 2.4V other inputs: at V _{CC} or GND I _{OUT} = 0μA	2.7	2.9	3.0	mA

AC ELECTRICAL CHARACTERISTICS (Input $t_r, t_f \leq 2\text{ ns}$, AHCT390)

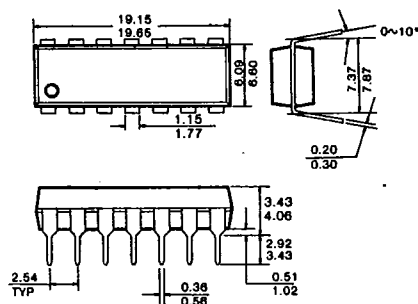
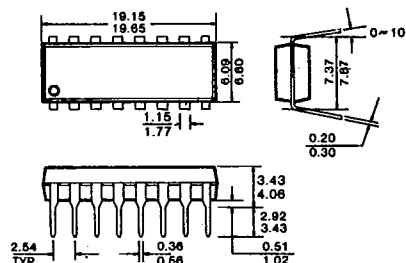
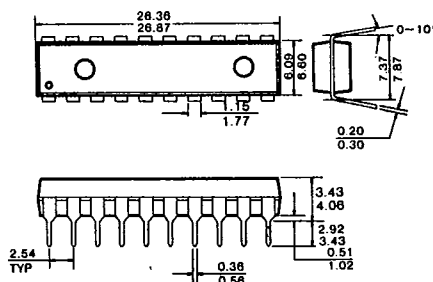
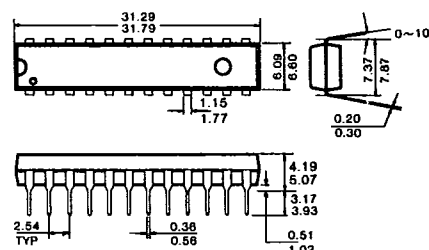
Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	$T_a = -40^\circ\text{C}$ to $+85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		$T_a = -55^\circ\text{C}$ to $+125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Propagation Delay, CKA to Q_A or CKB to Q_B	t_{max}	$C_L = 50\text{pF}$	50	30		25		MHz
Propagation Delay, CKA to Q_A	t_{PLH}		9		15		18	ns
	t_{PHL}		9		15		18	ns
Propagation Delay, CKA to Q_C	t_{PLH}		24		40		48	ns
	t_{PHL}		24		40		48	ns
Propagation Delay, CKB to Q_B	t_{PLH}		10		17		21	ns
	t_{PHL}		10		17		21	ns
Propagation Delay, CKB to Q_C	t_{PLH}		16		27		33	ns
	t_{PHL}		16		27		33	ns
Propagation Delay, CKB to Q_D	t_{PLH}		10		17		21	ns
	t_{PHL}		10		17		21	ns
Propagation Delay, CLR to Any Q	t_{PHL}		14		24		29	ns
Pulse Width	CKA or CKB High or Low CLR High	t_w	7	12		15		ns
			7	12		15		ns
Minimum Setup Time, CLR inactive before CKA or CKB	t_{SU}		5	8		10		ns
Input Capacitance	C_{IN}		5					pF
Power Dissipation Capacitance	C_{PD}							pF

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.



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PACKAGE DIMENSIONS*T-90-20***1. PLASTIC PACKAGES****14-Pin Plastic DIP Units: mm****16-Pin Plastic DIP Units: mm****20-Pin Plastic DIP Units: mm****24-Pin Plastic DIP Units: mm**

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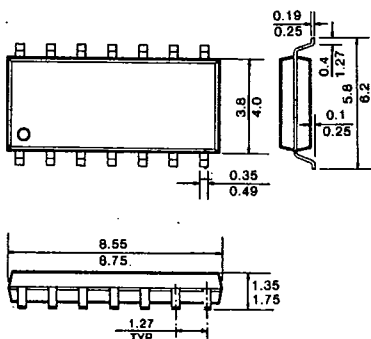
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PACKAGE DIMENSIONS

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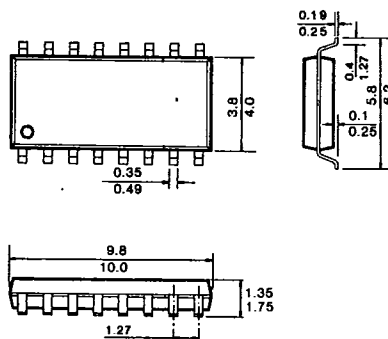
14-Pin SOP

Unit: mm



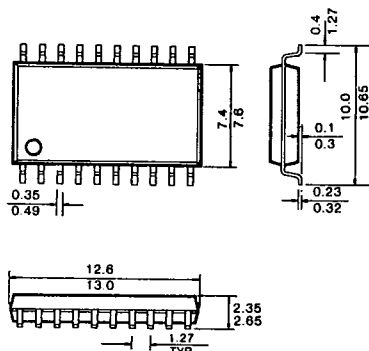
16-Pin SOP

Unit: mm



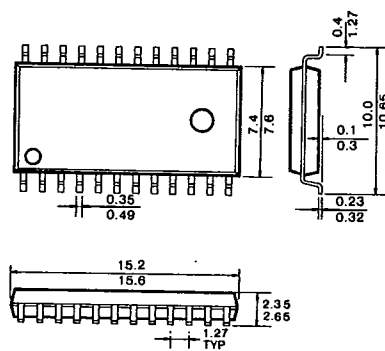
20-Pin SOP

Unit: mm



24-Pin SOP

Unit: mm



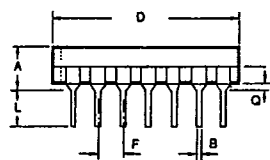
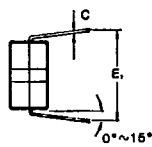
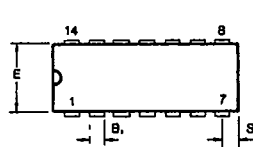
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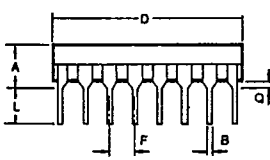
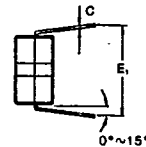
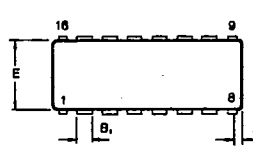
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PACKAGE DIMENSIONS

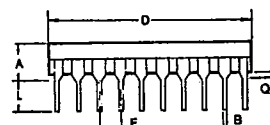
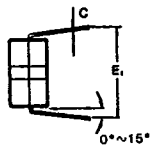
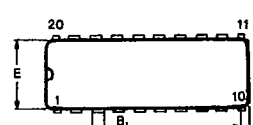
T-90-20

2. CERAMIC PACKAGES**14-Pin Ceramic DIP Units: mm**

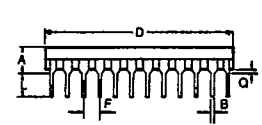
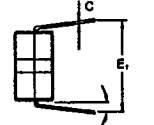
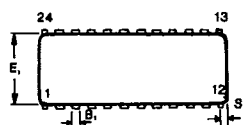
Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	8.10	8.60
E ₁	7.77	7.88
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.88
F	2.54	
L	3.73	4.01
Q	0.508	1.778
S	1.85	1.93

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